

REMARKS

Claims 69 and 74 are amended. Claims 1-8, 11-19, 21-32, 62-66, 70-73 and 75-80 are canceled herein. Claims 81-95 are added. Claims 69, 74, and 81-95 are in the application for consideration.

There remains two PTO Form-1449s properly submitted by Applicant which the undersigned has yet to receive initialed copies from the Examiner. Specifically, on March 10, 2003, and on February 2, 2004 Applicant submitted Supplemental Information Disclosure Statements. Duplicate copies of those Supplemental Information Disclosure Statements, including the PTO Form-1449s are included herewith. It is respectfully requested that the Examiner initial the enclosed Form-1449s and provide the undersigned with an initialed copy of each PTO Form-1449. A Supplemental Information Disclosure Statement and PTO-1449 is also submitted herewith.

Independent claim 69 stood rejected as being anticipated by U.S. Patent No. 6,350,655 to Mizuo. Claim 69 has been amended to recite that the masking layer comprises silicon nitride received over an oxide layer. Claim 69 is further amended to recite etching of the masking layer within a microwave power plasma etcher effective to expose semiconductive material of the semiconductor substrate using a first gas chemistry comprising CF₄ and CHF₃, a first magnetron power and a first RF power. Claim 69 is further amended to recite etching into semiconductive material of the semiconductor substrate within the microwave powered plasma etcher using a second gas chemistry comprising CF₄ and CHF₃, a second magnetron

pówer and a second RF power. Claim 69 is further amended to recite that the quantity of CF_4 is greater than the quantity of CHF_4 in the first gas chemistry, and that the quantity of the CHF_3 is greater than the quantity of CF_4 in the second gas chemistry. Claim 69 is further amended to recite that the second RF power is greater than the first RF power. Support for the same is inherent from Applicant's application as filed at, for example, p.9, Ins.7-9 and col.10, Ins.6-17.

Amended claim 69 is neither anticipated nor obvious over any one or combination of the cited references. For example, and by way of example only, the cited Mizuo patent in no way discloses use of Applicant's claim 69 recited chemistry or conditions. The same applies to the applied Liu et al. and Yu et al. references. Further, and by way of example only, Yu et al. in no way discloses or suggests etching into its disclosed semiconductor material utilizing any CF_4 and CHF_3 . Fig. 2 and the text pertaining thereto of Yu et al. clearly in combination shows that the Fig. 1 etching stops on material 1 and that thereafter polymer material 6b forms. Fig. 2 clearly shows a lack of etching of material 1. Further, col.3, Ins.34-40 clearly only discloses forming trench 7 of Fig. 3 utilizing a different chemistry from CF_4 and CHF_3 . Applicant's claim 69 recitations are more than mere matters of design choice as respect type of etcher, quantity of CHF_3 and the respective differences in RF power. The variously recited references are lacking in disclosure relative to all of the elements of independent claim 69.

Accordingly, such claim should be allowed, and action to that end is requested.

Applicant's dependent claim should be allowed as depending from allowable base claims and for their own recited features which are neither shown nor suggested in the cited art. Action to that end is requested. The newly added claims are either taken from other claims or supported by the table in Applicant's application as filed at page 10.

This application is believed to be in immediate condition for allowance.

Respectfully submitted,

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By: 

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